



**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) An image sensor comprising:
  - (a) a semi-conducting substrate having a photo-sensitive region and doping for forming a path to a charge-to-voltage mechanism;
  - (b) a dielectric spanning the substrate; and
  - (c) a single crystal semi-conducting layer, which is less than approximately 1 micrometer, spanning the dielectric which contains electrodes and circuit elements that control flow of charge.
2. (Original) The image sensor as in claim 1, wherein the semi-conducting substrate and semi-conducting layer are silicon.
3. (Original) The image sensor as in claim 2, wherein the dielectric is silicon dioxide.
4. (Original) The image sensor as in claim 3, wherein the semi-conducting substrate includes an epitaxial layer.
5. (Original) The image sensor as in claim 1 further comprising doping for a reset transistor in the semi-conducting substrate and a reset gate in the semi-conducting layer.
6. (Original) The image sensor as a claim 1, wherein the photo-sensitive region is a photodiode.
7. (Original) The image sensor as in claim 1, wherein the charge-to-voltage mechanism is a floating diffusion.
8. (Original) The image sensor as in claim 1, wherein the image sensor is a CMOS image sensor.

9-11. (Canceled)

12. (Currently Amended) A camera comprising:  
an image sensor comprising:

- (a) a semi-conducting substrate having a photo-sensitive region and doping for forming a path to a charge-to-voltage mechanism;
- (b) a dielectric spanning the substrate; and
- (c) a single crystal semi-conducting layer, which is less than approximately 1 micrometer, spanning the dielectric which contains electrodes and circuit elements that control flow of charge.

13. (Original) The camera as in claim 12, wherein the semi-conducting substrate and semi-conducting layer are silicon.

14. (Original) The camera as in claim 13, wherein the dielectric is silicon dioxide.

15. (Original) The camera as in claim 14, wherein the semi-conducting substrate includes an epitaxial layer.

16. (Original) The camera as in claim 12 further comprising doping for a reset transistor in the semi-conducting substrate and a reset gate in the semi-conducting layer.

17. (Original) The camera as in claim 12, wherein the photo-sensitive region is a photodiode.

18. (Original) The camera as in claim 12, wherein the charge-to-voltage mechanism is a floating diffusion.

19. (Original) The camera as in claim 12, wherein the image sensor is a CMOS image sensor.

**Amendments to the Drawings:**

Formal drawings are submitted herewith under Separate Letter to the Draftsperson. For the convenience of the Examiner, a copy of the formal drawings are also attached with this amendment.

**Attachment: Replacement Figures 1-3**